

# IRLB8721PbF

HEXFET® Power MOSFET

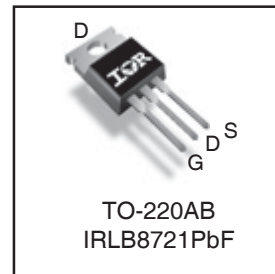
## Applications

- Optimized for UPS/Inverter Applications
- High Frequency Synchronous Buck Converters for Computer Processor Power
- High Frequency Isolated DC-DC Converters with Synchronous Rectification for Telecom and Industrial Use

V <sub>DSS</sub>	R <sub>DS(on)</sub> max	Qg (typ.)
30V	8.7mΩ @ V <sub>GS</sub> = 10V	7.6nC

## Benefits

- Very Low RDS(on) at 4.5V V<sub>GS</sub>
- Ultra-Low Gate Impedance
- Fully Characterized Avalanche Voltage and Current
- Lead-Free



G	D	S
Gate	Drain	Source

## Absolute Maximum Ratings

	Parameter	Max.	Units		
V <sub>DS</sub>	Drain-to-Source Voltage	30	V		
V <sub>GS</sub>	Gate-to-Source Voltage	± 20			
I <sub>D</sub> @ T <sub>C</sub> = 25°C	Continuous Drain Current, V <sub>GS</sub> @ 10V	62	A		
I <sub>D</sub> @ T <sub>C</sub> = 100°C	Continuous Drain Current, V <sub>GS</sub> @ 10V	44			
I <sub>DM</sub>	Pulsed Drain Current ①	250			
P <sub>D</sub> @ T <sub>C</sub> = 25°C	Maximum Power Dissipation ⑤	65	W		
P <sub>D</sub> @ T <sub>C</sub> = 100°C	Maximum Power Dissipation ⑤	33			
	Linear Derating Factor	0.43	W/°C		
T <sub>J</sub>	Operating Junction and Storage Temperature Range	-55 to + 175			
T <sub>STG</sub>					
				Soldering Temperature, for 10 seconds	300 (1.6mm from case)
				Mounting torque, 6-32 or M3 screw	10lb·in (1.1N·m)

## Thermal Resistance

	Parameter	Typ.	Max.	Units
R <sub>θJC</sub>	Junction-to-Case ⑤	—	2.3	°C/W
R <sub>θCS</sub>	Case-to-Sink, Flat Greased Surface	0.5	—	
R <sub>θJA</sub>	Junction-to-Ambient ④	—	62	

Notes ① through ⑤ are on page 9  
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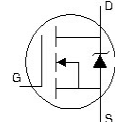
### Static @ T<sub>J</sub> = 25°C (unless otherwise specified)

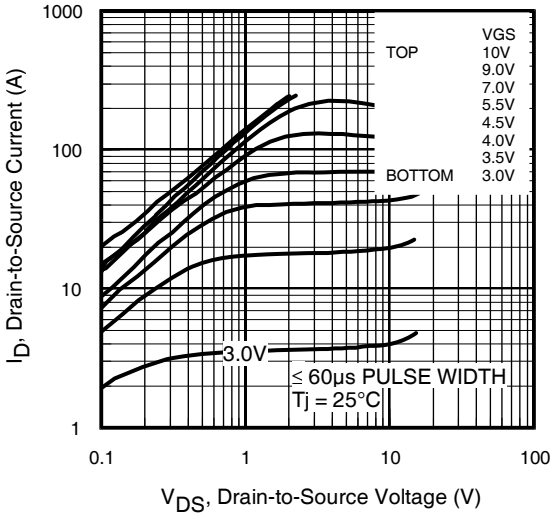
	Parameter	Min.	Typ.	Max.	Units	Conditions
BV <sub>DSS</sub>	Drain-to-Source Breakdown Voltage	30	—	—	V	V <sub>GS</sub> = 0V, I <sub>D</sub> = 250μA
ΔBV <sub>DSS</sub> /ΔT <sub>J</sub>	Breakdown Voltage Temp. Coefficient	—	21	—	mV/°C	Reference to 25°C, I <sub>D</sub> = 1mA
R <sub>DS(on)</sub>	Static Drain-to-Source On-Resistance	—	6.5	8.7	mΩ	V <sub>GS</sub> = 10V, I <sub>D</sub> = 31A ③
		—	13.1	16		V <sub>GS</sub> = 4.5V, I <sub>D</sub> = 25A ③
V <sub>GS(th)</sub>	Gate Threshold Voltage	1.35	1.80	2.35	V	V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = 25μA
ΔV <sub>GS(th)</sub> /ΔT <sub>J</sub>	Gate Threshold Voltage Coefficient	—	-7.0	—	mV/°C	
I <sub>DSS</sub>	Drain-to-Source Leakage Current	—	—	1.0	μA	V <sub>DS</sub> = 24V, V <sub>GS</sub> = 0V
		—	—	150		V <sub>DS</sub> = 24V, V <sub>GS</sub> = 0V, T <sub>J</sub> = 125°C
I <sub>GSS</sub>	Gate-to-Source Forward Leakage	—	—	100	nA	V <sub>GS</sub> = 20V
	Gate-to-Source Reverse Leakage	—	—	-100		V <sub>GS</sub> = -20V
g <sub>fs</sub>	Forward Transconductance	35	—	—	S	V <sub>DS</sub> = 15V, I <sub>D</sub> = 25A
Q <sub>g</sub>	Total Gate Charge	—	7.6	13	nC	V <sub>DS</sub> = 15V V <sub>GS</sub> = 4.5V I <sub>D</sub> = 25A See Fig. 16
Q <sub>gs1</sub>	Pre-V <sub>th</sub> Gate-to-Source Charge	—	1.9	—		
Q <sub>gs2</sub>	Post-V <sub>th</sub> Gate-to-Source Charge	—	1.2	—		
Q <sub>gd</sub>	Gate-to-Drain Charge	—	3.4	—		
Q <sub>godr</sub>	Gate Charge Overdrive	—	2.0	—		
Q <sub>sw</sub>	Switch Charge (Q <sub>gs2</sub> + Q <sub>gd</sub> )	—	4.6	—		
Q <sub>oss</sub>	Output Charge	—	7.9	—	nC	V <sub>DS</sub> = 15V, V <sub>GS</sub> = 0V
R <sub>G</sub>	Gate Resistance	—	2.3	3.8	Ω	
t <sub>d(on)</sub>	Turn-On Delay Time	—	9.1	—	ns	V <sub>DD</sub> = 15V, V <sub>GS</sub> = 4.5V ③ I <sub>D</sub> = 25A R <sub>G</sub> = 1.8Ω See Fig. 14
t <sub>r</sub>	Rise Time	—	93	—		
t <sub>d(off)</sub>	Turn-Off Delay Time	—	9.0	—		
t <sub>f</sub>	Fall Time	—	17	—		
C <sub>iss</sub>	Input Capacitance	—	1077	—	pF	V <sub>GS</sub> = 0V V <sub>DS</sub> = 15V f = 1.0MHz
C <sub>oss</sub>	Output Capacitance	—	360	—		
C <sub>rss</sub>	Reverse Transfer Capacitance	—	110	—		

### Avalanche Characteristics

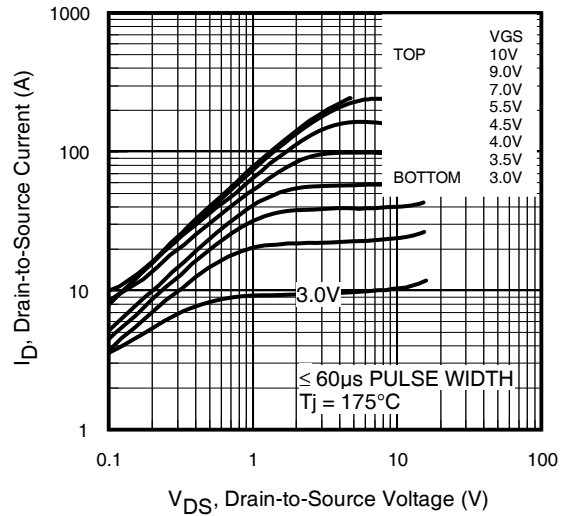
	Parameter	Typ.	Max.	Units
E <sub>AS</sub>	Single Pulse Avalanche Energy ②	—	98	mJ
I <sub>AR</sub>	Avalanche Current ①	—	25	A

### Diode Characteristics

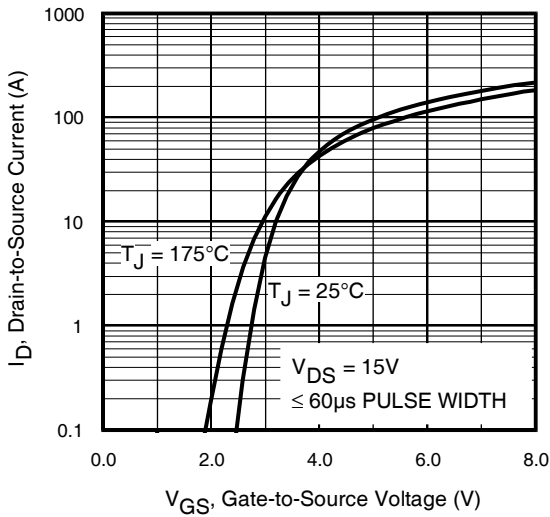
	Parameter	Min.	Typ.	Max.	Units	Conditions
I <sub>S</sub>	Continuous Source Current (Body Diode)	—	—	62	A	MOSFET symbol showing the integral reverse p-n junction diode. 
I <sub>SM</sub>	Pulsed Source Current (Body Diode) ①	—	—	250		
V <sub>SD</sub>	Diode Forward Voltage	—	—	1.0	V	T <sub>J</sub> = 25°C, I <sub>S</sub> = 25A, V <sub>GS</sub> = 0V ③
t <sub>rr</sub>	Reverse Recovery Time	—	16	24	ns	T <sub>J</sub> = 25°C, I <sub>F</sub> = 25A, V <sub>DD</sub> = 15V
Q <sub>rr</sub>	Reverse Recovery Charge	—	14	21	nC	di/dt = 200A/μs ③



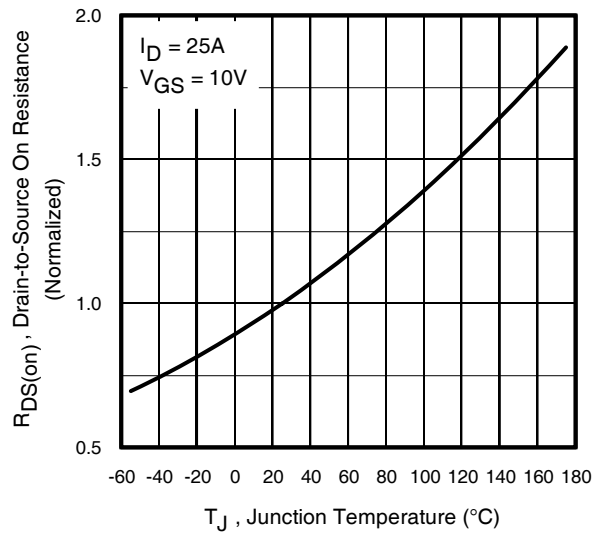
**Fig 1.** Typical Output Characteristics



**Fig 2.** Typical Output Characteristics

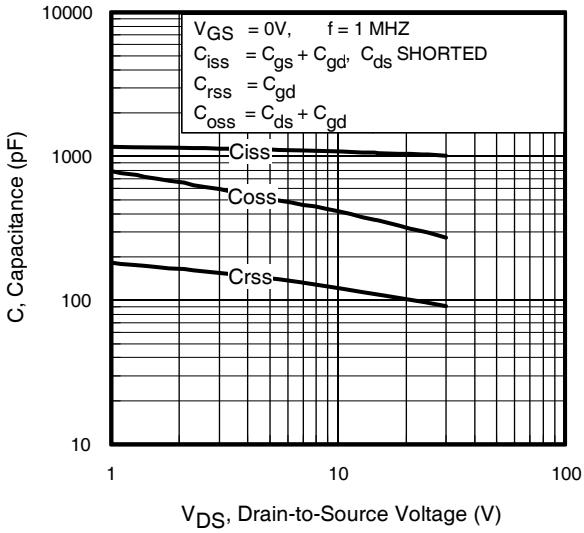


**Fig 3.** Typical Transfer Characteristics

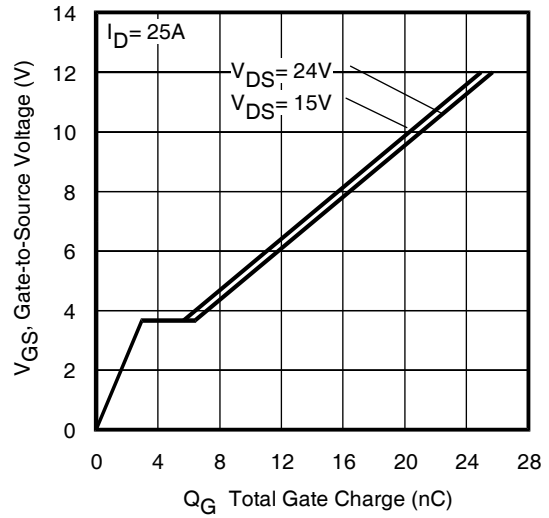


**Fig 4.** Normalized On-Resistance vs. Temperature

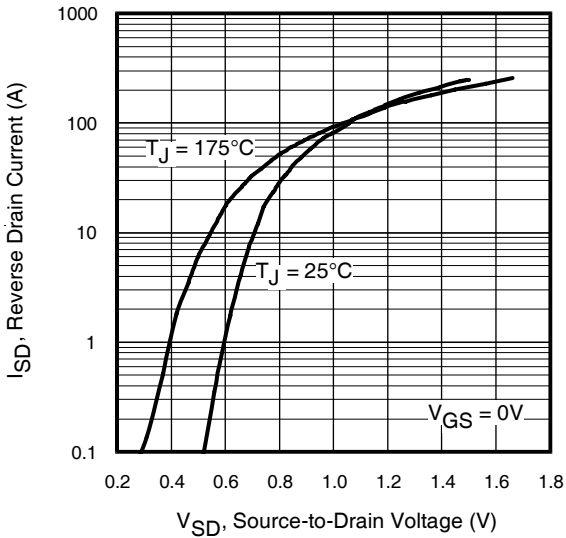
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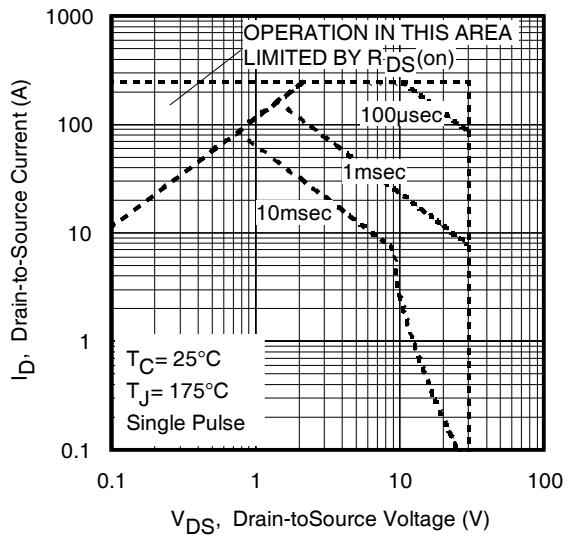
**Fig 5.** Typical Capacitance vs. Drain-to-Source Voltage



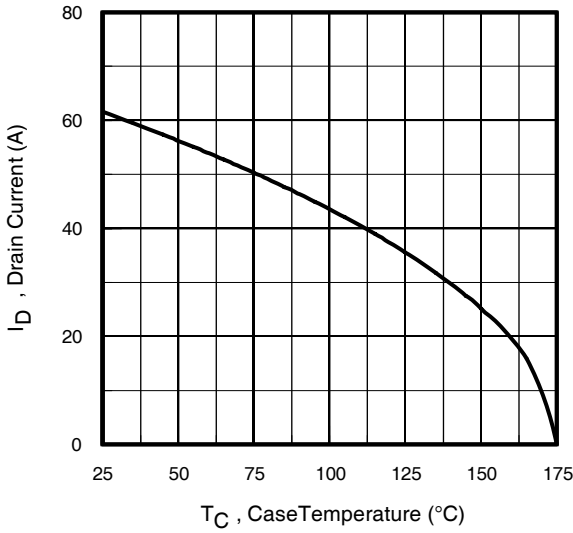
**Fig 6.** Typical Gate Charge vs. Gate-to-Source Voltage



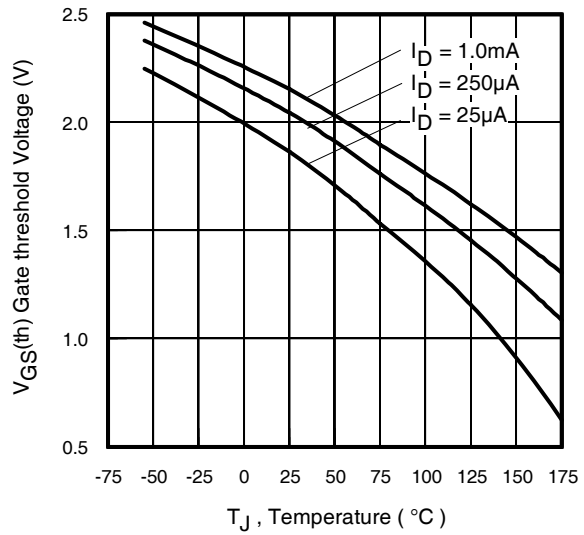
**Fig 7.** Typical Source-Drain Diode Forward Voltage



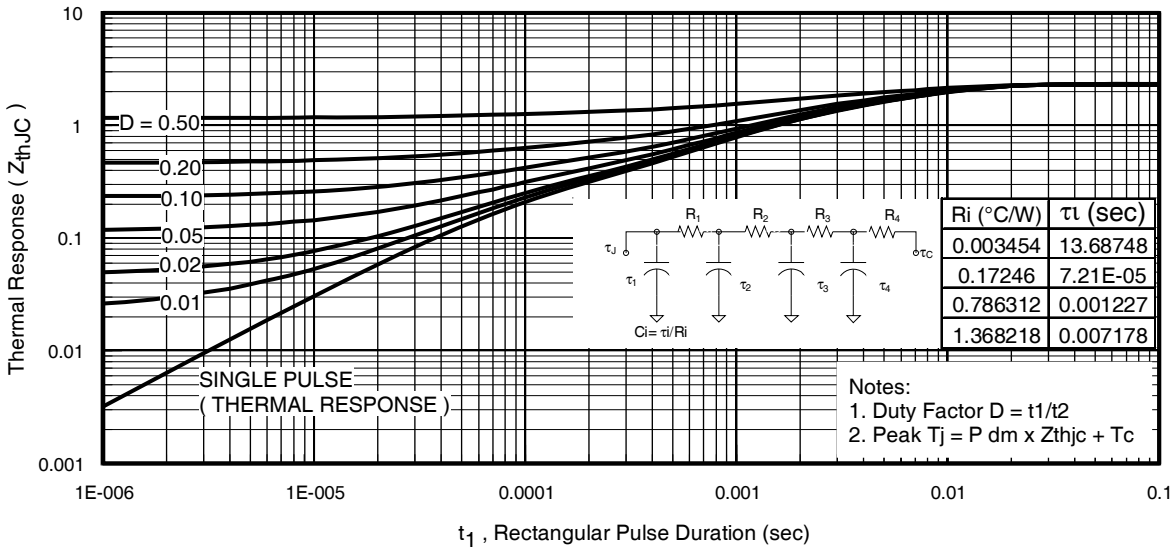
**Fig 8.** Maximum Safe Operating Area



**Fig 9.** Maximum Drain Current vs. Case Temperature



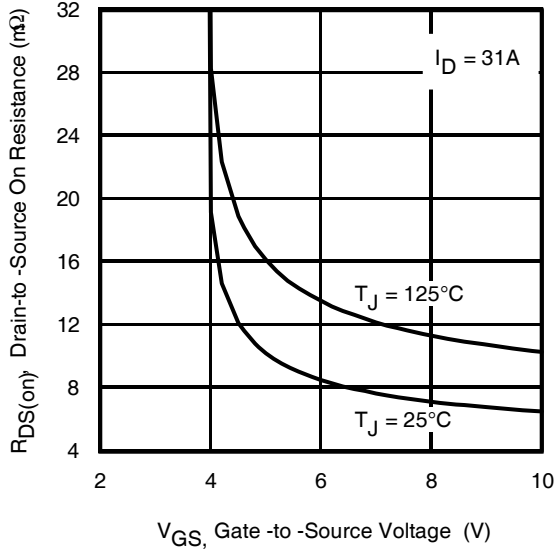
**Fig 10.** Threshold Voltage vs. Temperature



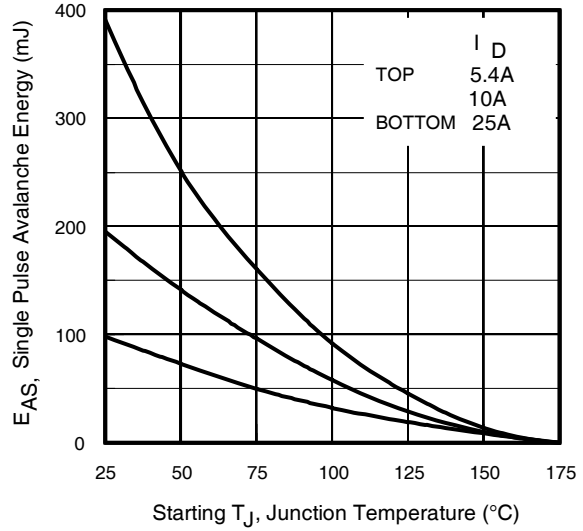
**Fig 11.** Maximum Effective Transient Thermal Impedance, Junction-to-Case

# IRLB8721PbF

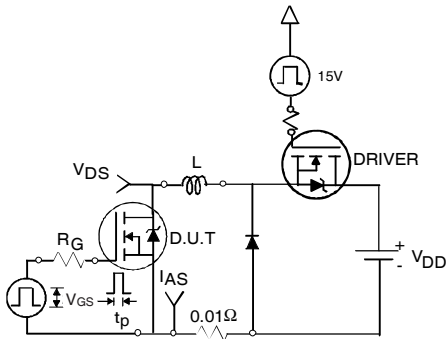
International  
**IR** Rectifier



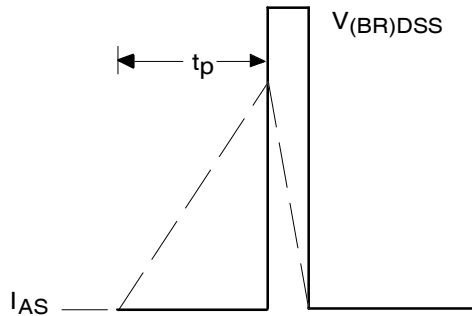
**Fig 12.** On-Resistance vs. Gate Voltage



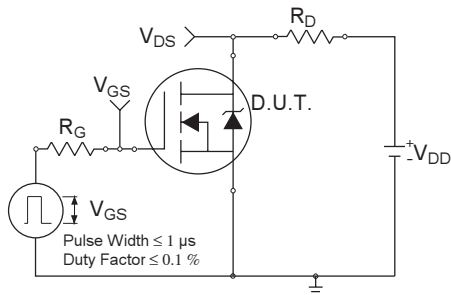
**Fig 13a.** Maximum Avalanche Energy vs. Drain Current



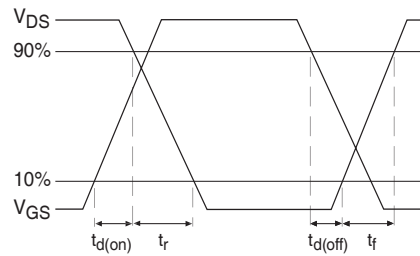
**Fig 13b.** Unclamped Inductive Test Circuit



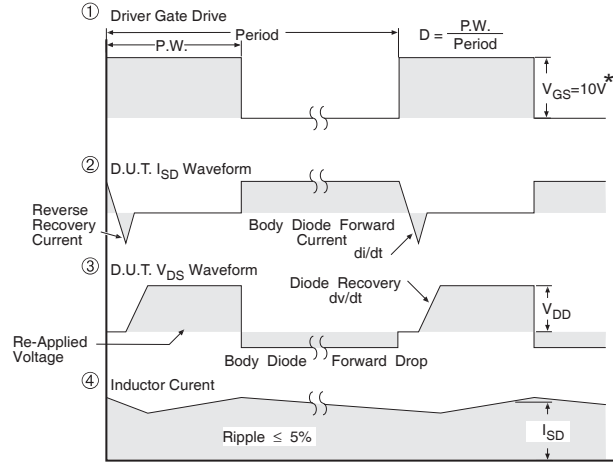
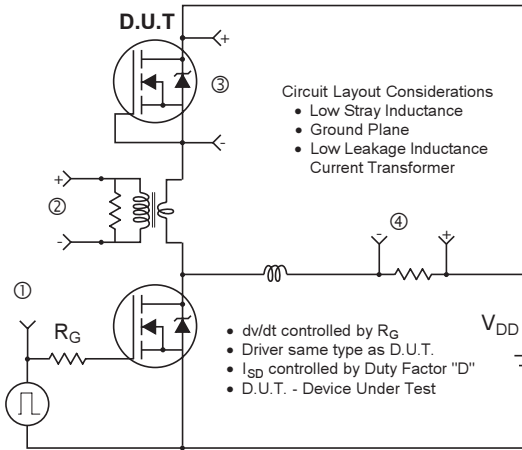
**Fig 13c.** Unclamped Inductive Waveforms



**Fig 14a.** Switching Time Test Circuit

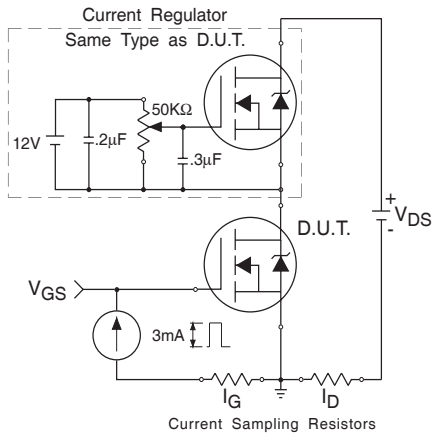


**Fig 14b.** Switching Time Waveforms

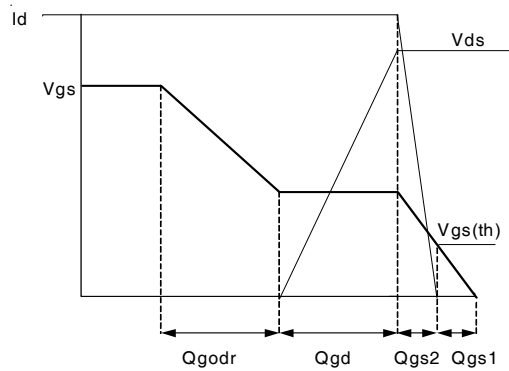


\*  $V_{GS} = 5V$  for Logic Level Devices

**Fig 15. Peak Diode Recovery  $dv/dt$  Test Circuit for N-Channel HEXFET<sup>®</sup> Power MOSFETs**



**Fig 16a. Gate Charge Test Circuit**

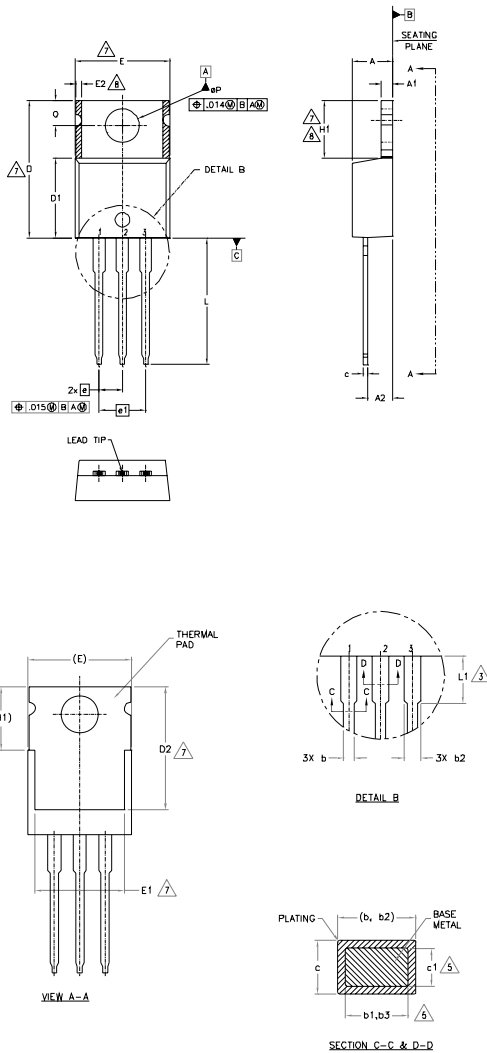


**Fig 16b. Gate Charge Waveform**

# IRLB8721PbF

International  
**IRF** Rectifier

TO-220AB Package Outline (Dimensions are shown in millimeters (inches))



**NOTES:**

- 1.- DIMENSIONING AND TOLERANCING AS PER ASME Y14.5 M- 1994.
- 2.- DIMENSIONS ARE SHOWN IN INCHES [MILLIMETERS].
- 3.- LEAD DIMENSION AND FINISH UNCONTROLLED IN L1.
- 4.- DIMENSION D, D1 & E DO NOT INCLUDE MOLD FLASH. MOLD FLASH SHALL NOT EXCEED .005" (0.127) PER SIDE. THESE DIMENSIONS ARE MEASURED AT THE OUTERMOST EXTREMES OF THE PLASTIC BODY.
- 5.- DIMENSION b1, b3 & c1 APPLY TO BASE METAL ONLY.
- 6.- CONTROLLING DIMENSION : INCHES.
- 7.- THERMAL PAD CONTOUR OPTIONAL WITHIN DIMENSIONS E,H1,D2 & E1
- 8.- DIMENSION E2 X H1 DEFINE A ZONE WHERE STAMPING AND SINGULATION IRREGULARITIES ARE ALLOWED.
- 9.- OUTLINE CONFORMS TO JEDEC TO-220, EXCEPT A2 (max.) AND D2 (min.) WHERE DIMENSIONS ARE DERIVED FROM THE ACTUAL PACKAGE OUTLINE.

SYMBOL	DIMENSIONS				NOTES
	MILLIMETERS		INCHES		
	MIN.	MAX.	MIN.	MAX.	
A	3.56	4.83	.140	.190	
A1	0.51	1.40	.020	.055	
A2	2.03	2.92	.080	.115	
b	0.38	1.01	.015	.040	
b1	0.38	0.97	.015	.038	5
b2	1.14	1.78	.045	.070	
b3	1.14	1.73	.045	.068	5
c	0.36	0.61	.014	.024	
c1	0.36	0.56	.014	.022	5
D	14.22	16.51	.560	.650	4
D1	8.38	9.02	.330	.356	
D2	11.68	12.88	.460	.507	7
E	9.65	10.67	.380	.420	4,7
E1	6.86	8.89	.270	.350	7
E2	-	0.76	-	.030	8
e	2.54 BSC		.100 BSC		
e1	5.08 BSC		.200 BSC		
H1	5.84	6.86	.230	.270	7,8
L	12.70	14.73	.500	.580	
L1	3.56	4.06	.140	.160	3
ØP	3.54	4.08	.139	.161	
Q	2.54	3.42	.100	.135	

**LEAD ASSIGNMENTS**

**HEXFET**

- 1.- GATE
- 2.- DRAIN
- 3.- SOURCE

**IGBTs, CoPACK**

- 1.- GATE
- 2.- COLLECTOR
- 3.- EMITTER

**DIODES**

- 1.- ANODE
- 2.- CATHODE
- 3.- ANODE

TO-220AB packages are not recommended for Surface Mount Application.

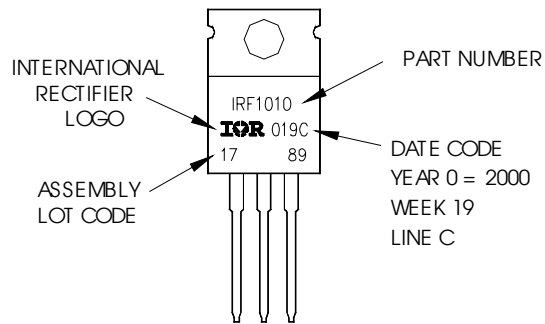
Note: For the most current drawing please refer to IR website at: <http://www.irf.com/package/>



## TO-220AB Part Marking Information

EXAMPLE: THIS IS AN IRF1010  
LOT CODE 1789  
ASSEMBLED ON WW 19, 2000  
IN THE ASSEMBLY LINE "C"

Note: "P" in assembly line position  
indicates "Lead - Free"



**Note:** For the most current drawing please refer to IR website at: <http://www.irf.com/package/>

### Notes:

- ① Repetitive rating; pulse width limited by max. junction temperature.
- ② Starting  $T_J = 25^\circ\text{C}$ ,  $L = 0.32\text{mH}$ ,  $R_G = 25\Omega$ ,  $I_{AS} = 25\text{A}$ .
- ③ Pulse width  $\leq 400\mu\text{s}$ ; duty cycle  $\leq 2\%$ .
- ④ When mounted on 1" square PCB (FR-4 or G-10 Material). For recommended footprint and soldering techniques refer to application note #AN-994.
- ⑤  $R_\theta$  is measured at  $T_J$  approximately  $90^\circ\text{C}$ .

Data and specifications subject to change without notice.  
This product has been designed and qualified for the Industrial market.  
Qualification Standards can be found on IR's Web site.

International  
**IR** Rectifier

**IR WORLD HEADQUARTERS:** 233 Kansas St., El Segundo, California 90245, USA Tel: (310) 252-7105  
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